

Rev.B Aug.-2025

SOT23-6 P MOS

P-CHANNEL MOSFET in a SOT23-6 Plastic Package.

$V_{DS} (V) = -16V$ $I_D = -7.0A$

$R_{DS(ON)} @ -4.5V(Typ.) = 16.7m$

$R_{DS(ON)} @ -2.5V(Typ.) = 22.5m$

$R_{DS(ON)} @ -1.8V(Typ.) = 32.5m$

HF Product.

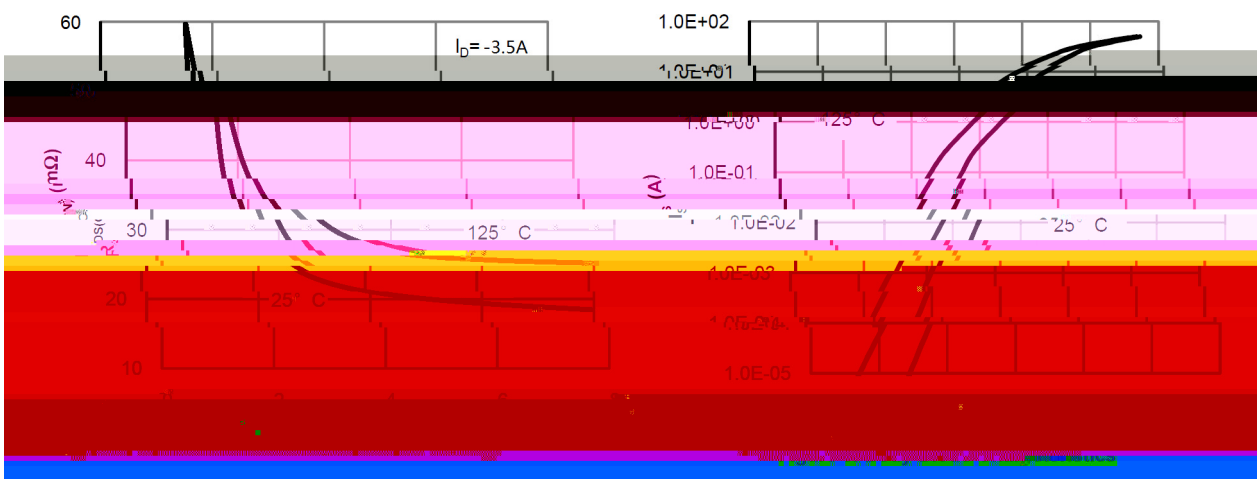
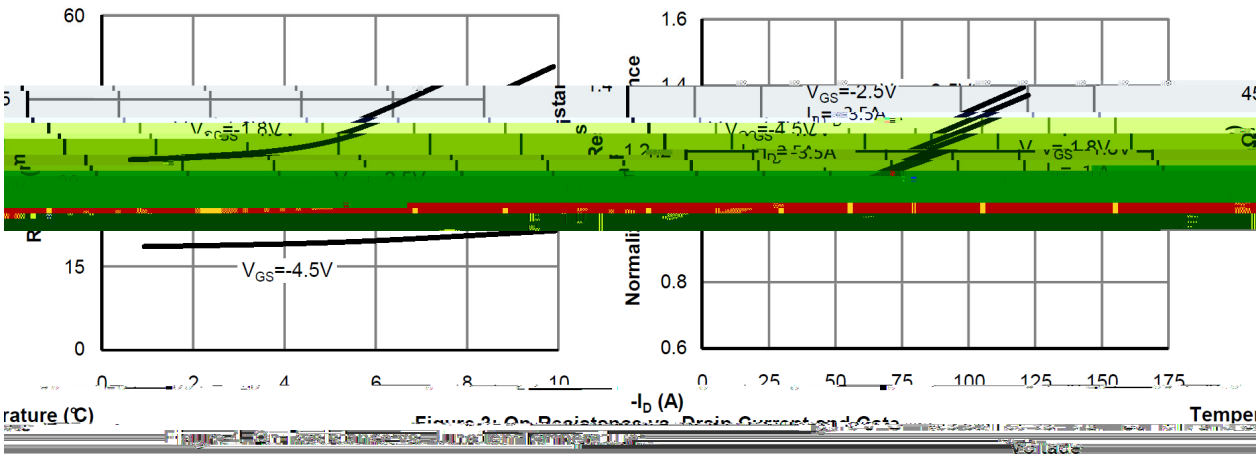
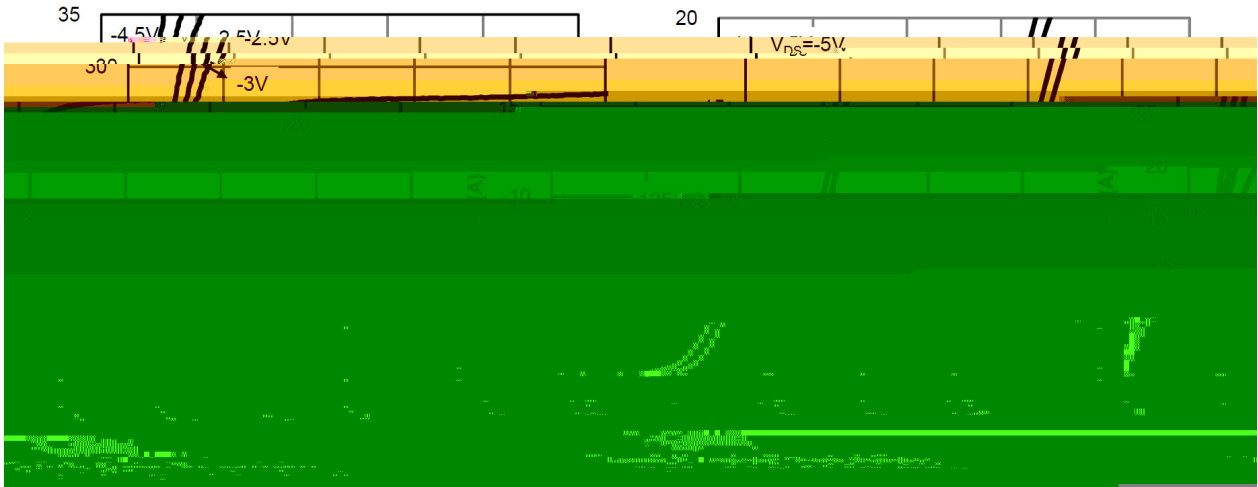
Power Management in Notebook computer, Portable Equipment and Battery powered systems.

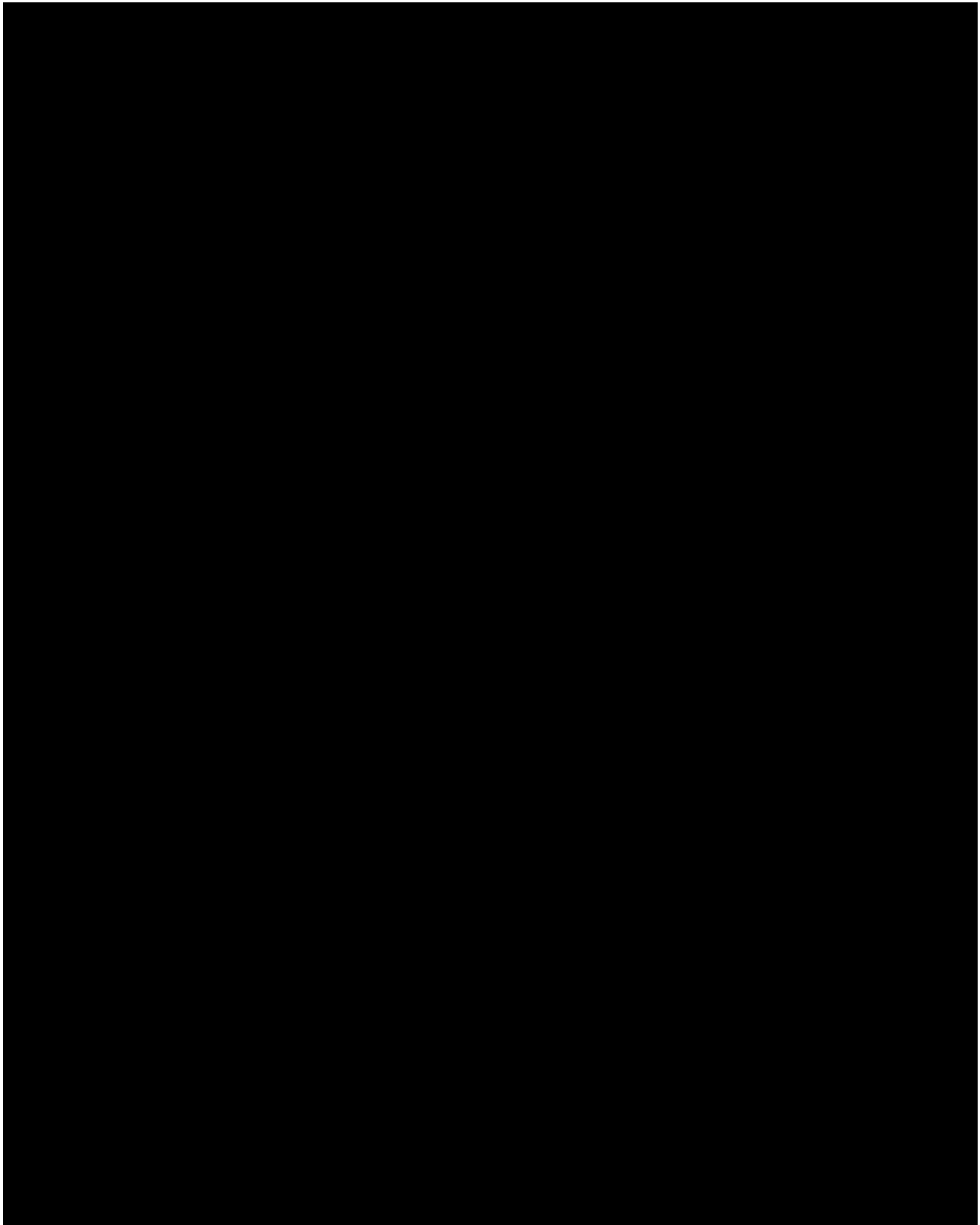
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current	I_D	-7.0	A
Pulsed Drain Current	I_{DM}	-30	A
Power Dissipation for Single Operation	P_D	1.2	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance-Junction to Ambient	R_{JA}	100	/W

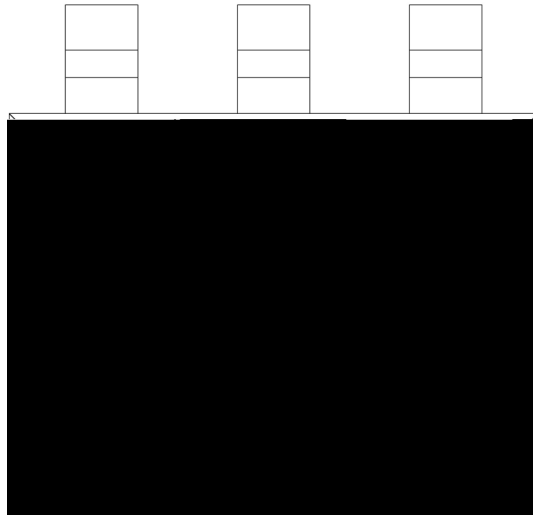
Parameter Symbol



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	$V_{GS}=-4.5V, V_{DS}=-10V, I_D=-7.0A$		13.2		nC
Gate Source Charge	Q_{gs}			1.5		
Gate Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-4.5V, I_D=-7.0A, V_{DS}=-10V, R_{GEN}=3$		13.7		ns
Turn-On Rise Time	t_r			47.6		
Turn-Off Delay Time	$t_{d(off)}$			43.1		
Turn-Off Fall Time	t_f			29.5		







C6

H

Note:

C6: Product Type Code

H: Company Code

